

## 100V 0.3A Fast Switching Diode - CD4148

Small-Signal high speed switching diode in bare die form

Rev 1.1 24/10/24

#### Features:

- Fast Switching Speed
- High conductance
- General purpose switching applications
- High reliability tested grades.

### **Ordering Information**

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

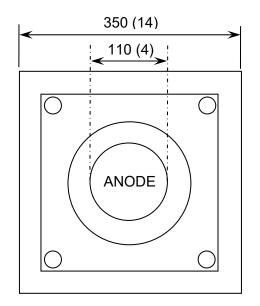
For further information on LAT process flows see below.

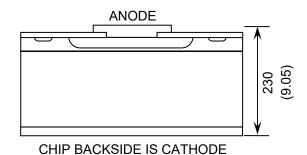
www.siliconsupplies.com\quality\bare-die-lot-qualification

### **Supply Formats:**

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- Die Thickness <> 230µm(9 Mils) On request
- With additional electrical selection On request

### Die Dimensions in µm (mils)





**Mechanical Specification** 

Die Size (Unsawn)	350 x 350 13.78 x 13.78	μm mils	
Anode Pad Size	110 Ø 4.3 Ø	μm mils	
Die Thickness	230 (±15) 9.05 (±0.59)	μm mils	
Top Metal Composition	Al		
Back Metal Composition	AuAs		





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### Absolute Maximum Ratings<sup>1</sup> T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	105	V
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current	I <sub>0</sub>	200	mA
DC Forward Current	I <sub>F</sub>	300	mA
Recurrent Peak Forward Current	lf	400	mA
Non-repetitive Peak forward surge current	l-o	Pulse width 1s 1	A
	I <sub>FSM</sub>	Pulse width 1µs 4	
Power Dissipation	$P_D$	200	mW
Operating Junction temperature	TJ	-55 to 175	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 200	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown Voltage	V <sub>R</sub>	I <sub>R</sub> = 100μA	100	-	-	V
	VR	I <sub>R</sub> = 5μΑ	75	-	-	V
Forward Voltage <sup>2</sup>		I <sub>F</sub> = 5mA	-	-	0.72	V
	V <sub>F</sub>	I <sub>F</sub> = 20mA	-	-	1	
		I <sub>F</sub> = 100mA	-	-	1	
Reverse Leakage		V <sub>R</sub> = 20V	-	-	0.025	μА
	I <sub>R</sub>	V <sub>R</sub> = 20V, T <sub>J</sub> = 150°C	-	-	50	
	ir [	V <sub>R</sub> = 75V	-	-	5	
		V <sub>R</sub> = 100V	-	-	10	
Total Capacitance	C <sub>T</sub>	$V_R = 0V$ , $f = 1MHz$	-	-	4	pF
Reverse Recovery Time	t <sub>rr</sub>	$I_F = 10mA, V_R = 6V (600mA)$ $I_{rr} = 1mA, R_L = 100\Omega$	-	-	4	ns

<sup>2.</sup> Pulse Width = 8.3ms, Non-recurrent square wave





## 100V 0.3A Fast Switching Diode - CD4148

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

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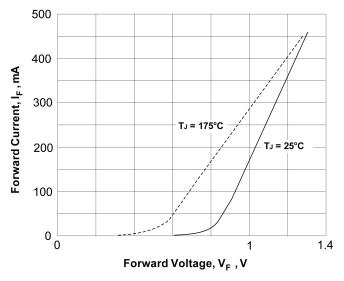


FIGURE 1. Forward Voltage Characteristics

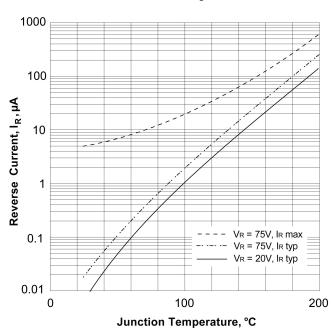


FIGURE 2. Leakage Current Versus Temperature

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